JFET Switching Transistors

N–Channel

Features

• These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	30	Vdc
Drain-Gate Voltage	V _{DG}	30	Vdc
Gate-Source Voltage	V _{GS}	30	Vdc
Forward Gate Current	I _{G(f)}	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

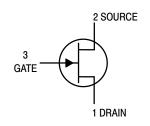
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

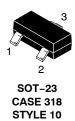
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.



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MARKING DIAGRAM



XXX = Specific Device Code M = Date Code* • = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

MARKING & ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS			•	•	•
Gate–Source Breakdown Voltage $(I_G = 1.0 \ \mu Adc, V_{DS} = 0)$		V _{(BR)GSS}	30	-	Vdc
Gate Reverse Current ($V_{GS} = 15 \text{ Vdc}, V_{DS} = 0, T_A = 25^{\circ}\text{C}$) ($V_{GS} = 15 \text{ Vdc}, V_{DS} = 0, T_A = 100^{\circ}\text{C}$)		I _{GSS}		1.0 0.20	nAdc μAdc
Gate-Source Cutoff Voltage (V _{DS} = 15 Vdc, I _D = 10 nAdc)	MMBF4391LT1 MMBF4392LT1 MMBF4393LT1	V _{GS(off)}	-4.0 -2.0 -0.5	-10 -5.0 -3.0	Vdc
$ \begin{array}{l} \mbox{Off-State Drain Current} \\ (V_{DS} = 15 \mbox{ Vdc}, \mbox{ V}_{GS} = -12 \mbox{ Vdc}) \\ (V_{DS} = 15 \mbox{ Vdc}, \mbox{ V}_{GS} = -12 \mbox{ Vdc}, \mbox{ T}_{A} = 100^{\circ}\mbox{C}) \end{array} $		I _{D(off)}		1.0 1.0	nAdc μAdc
ON CHARACTERISTICS			•		
Zero-Gate-Voltage Drain Current (V _{DS} = 15 Vdc, V _{GS} = 0)	MMBF4391LT1 MMBF4392LT1 MMBF4393LT1	I _{DSS}	50 25 5.0	150 75 30	mAdc
	MMBF4391LT1 MMBF4392LT1 MMBF4393LT1	V _{DS(on)}	- - -	0.4 0.4 0.4	Vdc
Static Drain–Source On–Resistance $(I_D = 1.0 \text{ mAdc}, V_{GS} = 0)$	MMBF4391LT1 MMBF4392LT1 MMBF4393LT1	r _{DS(on)}		30 60 100	Ω
SMALL-SIGNAL CHARACTERISTICS			•		•
Input Capacitance $(V_{DS} = 0 \text{ Vdc}, V_{GS} = -15 \text{ Vdc}, f = 1.0 \text{ MHz})$		C _{iss}	-	14	pF
Reverse Transfer Capacitance (V _{DS} = 0 Vdc, V _{GS} = -12 Vdc, f = 1.0 MHz)		C _{rss}	-	3.5	pF

ORDERING INFORMATION

Device	Device Marking Package		Shipping [†]	
MMBF4391LT1G	6J	SOT-23 (Pb-Free)		
MMBF4392LT1G	6K	SOT-23 (Pb-Free)	3000 / Tape & Reel	
MMBF4393LT1G	M6G	SOT-23 (Pb-Free)		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

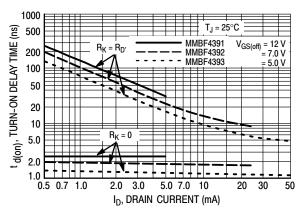


Figure 1. Turn-On Delay Time

t_{d(off)}, TURN-OFF DELAY TIME (ns)

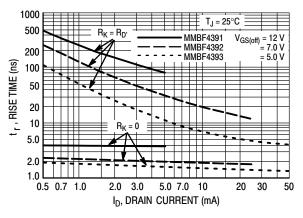


Figure 2. Rise Time

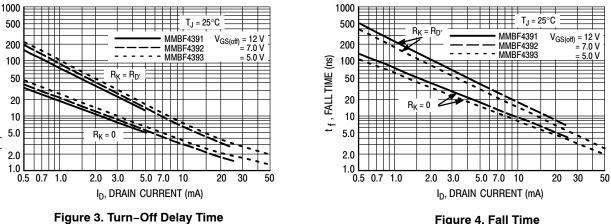


Figure 4. Fall Time

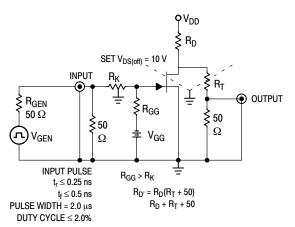


Figure 5. Switching Time Test Circuit

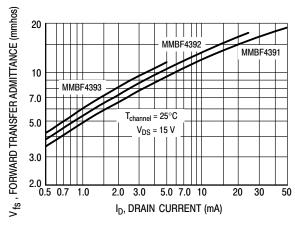


Figure 6. Typical Forward Transfer Admittance

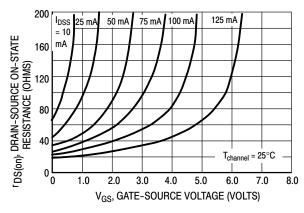


Figure 8. Effect of Gate-Source Voltage on Drain-Source Resistance

NOTE 1

The switching characteristics shown above were measured using a test circuit similar to Figure 5. At the beginning of the switching interval, the gate voltage is at Gate Supply Voltage ($-V_{GG}$). The Drain–Source Voltage (V_{DS}) is slightly lower than Drain Supply Voltage (V_{DD}) due to the voltage divider. Thus Reverse Transfer Capacitance (C_{rss}) of Gate–Drain Capacitance (C_{gd}) is charged to $V_{GG} + V_{DS}$.

During the turn–on interval, Gate–Source Capacitance (C_{gs}) discharges through the series combination of R_{Gen} and R_K . C_{gd} must discharge to $V_{DS(on)}$ through R_G and R_K in series with the parallel combination of effective load impedance (R'_D) and Drain–Source Resistance (r_{DS}). During the turn–off, this charge flow is reversed.

Predicting turn–on time is somewhat difficult as the channel resistance r_{DS} is a function of the gate–source voltage. While C_{gs} discharges, V_{GS} approaches zero and r_{DS} decreases. Since C_{gd} discharges through r_{DS} , turn–on time is non–linear. During turn–off, the situation is reversed with r_{DS} increasing as C_{gd} charges.

The above switching curves show two impedance conditions; 1) R_K is equal to $R_{D'}$ which simulates the switching behavior of cascaded stages where the driving source impedance is normally the load impedance of the previous stage, and 2) $R_K = 0$ (low impedance) the driving source impedance is that of the generator.

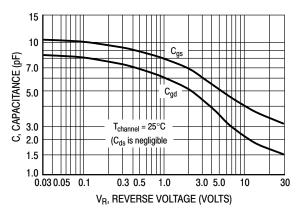
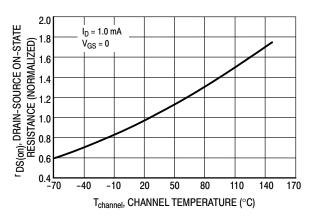
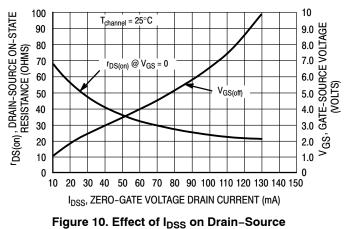


Figure 7. Typical Capacitance







Resistance and Gate-Source Voltage

NOTE 2

The Zero–Gate–Voltage Drain Current (I_{DSS}) is the principle determinant of other J–FET characteristics. Figure 10 shows the relationship of Gate–Source Off Voltage ($V_{GS(off)}$) and Drain–Source On Resistance ($r_{DS(on)}$) to I_{DSS} . Most of the devices will be within ±10% of the values shown in Figure 10. This data will be useful in predicting the characteristic variations for a given part number.

For example:

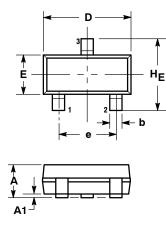
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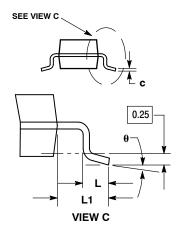
r_{DS(on)} and V_{GS} range for an MMBF4392

The electrical characteristics table indicates that an MMBF4392 has an I_{DSS} range of 25 to 75 mA. Figure 10 shows $r_{DS(on)} = 52 \Omega$ for I_{DSS} = 25 mA and 30 Ω for I_{DSS} = 75 mA. The corresponding V_{GS} values are 2.2 V and 4.8 V.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD
- FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. 318–01 THRU –07 AND –09 OBSOLETE, NEW STANDARD 318–08.

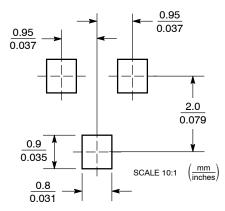
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
Г	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
ΗE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 10: PIN 1. DI

1. DRAIN 2. SOURCE

3. GATE

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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